NSN 5961-01-229-7317

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Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-229-7317 **Inclosure Material:** Glass **Overall Length:** 0.520 inches **Terminal Length:** 0.710 inches **Overall Diameter:** 1.250 inches **Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-36 **Response Time:** 7.0 nanoseconds **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 forward voltage, dc **Current Rating Per Characteristic:** 0.0002 milliamperes peak forward surge current peak **Power Rating Per Characteristic:** 0.5 watts small-signal input power, common-collector preset **Special Features:** Junction pattern arrangement: pn **Terminal Type And Quantity:** 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli Fiig: